



# **MMBT123S**

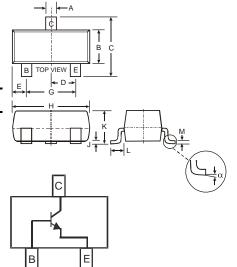
#### 1A NPN SURFACE MOUNT TRANSISTOR

#### **Features**

- **Epitaxial Planar Die Construction**
- Ideal for Medium Power Amplification and Switching
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2 and 4)

### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23								
Dim	Min	Max						
Α	0.37	0.51						
В	1.20	1.40						
С	2.30	2.50						
D	0.89	1.03						
E	0.45	0.60						
G	1.78	2.05						
Н	2.80	3.00						
J	0.013	0.10						
K	0.903	1.10						
L	0.45	0.61						
М	0.085	0.180						
α	0°	8°						
All Dimensions in mm								

## Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	45	V
Collector-Emitter Voltage	V <sub>CEO</sub>	18	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current - Continuous	Ic	1	Α
Power Dissipation (Note 1)	P <sub>D</sub>	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ heta JA}$	417	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

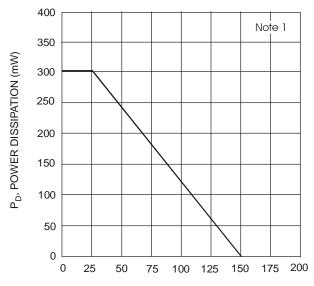
## **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)				-	
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	45	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	18	_	V	$I_{C} = 1 \text{mA}, I_{B} = 0$
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	5	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>	_	1	μΑ	$V_{CB} = 40V, I_{E} = 0$
Emitter Cutoff Current	I <sub>EBO</sub>	_	1	μΑ	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h <sub>FE</sub>	150	800	_	$I_C = 100 \text{mA}, V_{CE} = 1 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	0.5	V	$I_C = 300 \text{mA}, I_B = 30 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_obo$	_	8	pF	$V_{CB} = 10V$ , $f = 1.0MHz$ , $I_E = 0$
Current Gain-Bandwidth Product	f <sub>T</sub>	100	_	MHz	$V_{CB} = 10V, I_E = 50mA,$ f = 100MHz

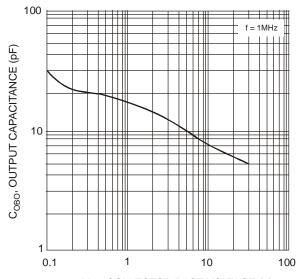
Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead. Halogen and Antimony Free.
- Short duration pulse test used to minimize self-heating effect.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.

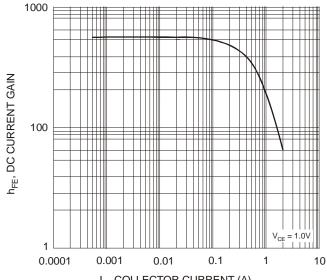




T<sub>A</sub>, AMBIENT TEMPERATURE (°C) Fig. 1, Max Power Dissipation vs Ambient Temperature



 $V_{CB}$ , COLLECTOR-BASE VOLTAGE (V) Fig. 3, Output Capacitance vs. Collector-Base Voltage



I<sub>C</sub>, COLLECTOR CURRENT (A) Fig. 2, Typical DC Current Gain vs Collector Current

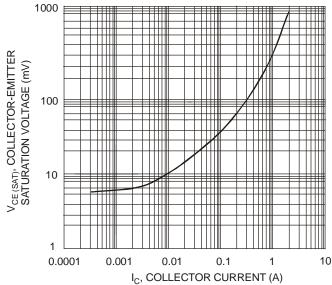


Fig. 4, Collector Saturation Voltage vs Collector Current

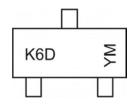


#### **Ordering Information** (Note 5)

Device	Packaging	Shipping			
MMBT123S-7-F	SOT-23	3000/Tape & Reel			

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

## **Marking Information**



K6D = Product Type Marking Code YM = Date Code Marking Y = Year ex: T = 2006 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	200	06 20	007	2008	2009	2010	2011	2012
Code	N	Р	R	S	Т		U	V	W	Χ	Υ	Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
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